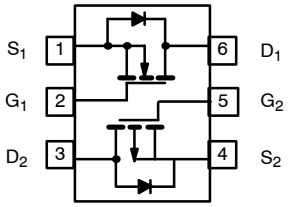
Complementary 20-V (D-S) Low-Threshold MOSFET

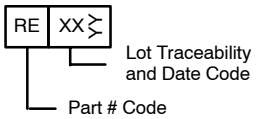
PRODUCT SUMMARY			
Channel	**V_{DS} (V)**	**$r_{DS(on)}$ (Ω)**	**I_D (mA)**
N-Channel	20	2.0 @ V_{GS} = 4.5 V	250
		2.5 @ V_{GS} = 2.5 V	150
P-Channel	−20	3.8 @ V_{GS} = −4.5 V	−180
		5.0 @ V_{GS} = −2.5 V	−100

SOT-363
SC-70 (6-Leads)



Top View

Marking Code



ABSOLUTE MAXIMUM RATINGS (T_A = 25°C UNLESS OTHERWISE NOTED)					
Parameter		**Symbol**	**N-Channel**	**P-Channel**	**Unit**
Drain-Source Voltage		V_{DS}	20	−20	V
Gate-Source Voltage		V_{GS}	±8	±8	
Continuous Drain Current (T_J = 150°C)[a]	T_A = 25°C	I_D	250	−180	mA
	T_A = 70°C		200	−140	
Pulsed Drain Current		I_{DM}	500	−500	
Maximum Power Dissipation[a]	T_A = 25°C	P_D	0.20		W
	T_A = 70°C		0.13		
Operating Junction and Storage Temperature Range		T_J, T_{stg}	−55 to 150		°C

THERMAL RESISTANCE RATINGS			
Parameter	**Symbol**	**Limit**	**Unit**
Maximum Junction-to-Ambient[a]	R_{thJA}	625 (Total)	°C/W

Notes
a. Surface Mounted on FR4 Board, t ≤ 10 sec.

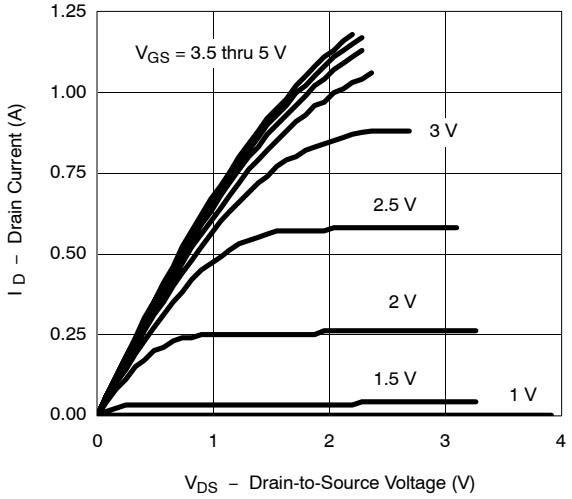
SPECIFICATIONS (T_J = 25°C UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
Static							
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 10 μA	N-Ch	20	24		V
		V_{GS} = 0 V, I_D = −10 μA	P-Ch	−20	−24		
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 50 μA	N-Ch	0.4	0.9	1.5	
		V_{DS} = V_{GS}, I_D = −50 μA	P-Ch	−0.4	−0.9	−1.5	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±8 V	N-Ch		±2	±100	nA
			P-Ch		±2	±100	
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 20 V, V_{GS} = 0 V	N-Ch		0.001	100	
		V_{DS} = −20 V, V_{GS} = 0 V	P-Ch		−0.001	−100	
		V_{DS} = 20 V, V_{GS} = 0 V, T_J = 55°C	N-Ch			1	μA
		V_{DS} = −20 V, V_{GS} = 0 V, T_J = 55°C	P-Ch			−1	
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} ≥ 2.5 V, V_{GS} = 5.0 V	N-Ch	120			mA
		V_{DS} ≤ −2.5 V, V_{GS} = −5.0 V	P-Ch	−120			
		V_{DS} ≥ 4.5 V, V_{GS} = 8.0 V	N-Ch	400			
		V_{DS} ≤ −4.5 V, V_{GS} = −8.0 V	P-Ch	−400			
Drain-Source On-State Resistance[a]	$r_{DS(on)}$	V_{GS} = 2.5 V, I_D = 150 mA	N-Ch		1.6	2.5	Ω
		V_{GS} = −2.5 V, I_D = −75 mA	P-Ch		4	5	
		V_{GS} = 4.5 V, I_D = 250 mA	N-Ch		1.2	2.0	
		V_{GS} = −4.5 V, I_D = −180 mA	P-Ch		2.6	3.8	
Forward Transconductance[a]	g_{fs}	V_{DS} = 2.5 V, I_D = 50 mA	N-Ch		150		mS
		V_{DS} = −2.5 V, I_D = − 50 mA	P-Ch		200		
Diode Forward Voltage[a]	V_{SD}	I_S = 50 mA, V_{GS} = 0 V	N-Ch		0.7	1.2	V
		I_S = −50 mA, V_{GS} = 0 V	P-Ch		−0.7	−1.2	
Dynamic[b]							
Total Gate Charge	Q_g	N-Channel V_{DS} = 5 V, V_{GS} = 4.5 V, I_D = 100 mA P-Channel V_{DS} = −5 V, V_{GS} = −4.5 V, I_D = −100 mA	N-Ch		300	450	pC
			P-Ch		300	450	
Gate-Source Charge	Q_{gs}		N-Ch		25		
			P-Ch		25		
Gate-Drain Charge	Q_{gd}		N-Ch		100		
			P-Ch		100		
Input Capacitance	C_{iss}	N-Channel V_{DS} = 5 V, V_{GS} = 0 V P-Channel V_{DS} = −5 V, V_{GS} = 0 V	N-Ch		15		pF
			P-Ch		15		
Output Capacitance	C_{oss}		N-Ch		11		
			P-Ch		11		
Reverse Transfer Capacitance	C_{rss}		N-Ch		5		
			P-Ch		5		
Switching							
Turn-On Time	$t_{d(on)}$	N-Channel V_{DD} = 3 V, R_L = 100 Ω I_D = 0.25 A, V_{GEN} = 4.5 V, R_g = 10 Ω P-Channel V_{DD} = −3 V, R_L = 100 Ω I_D = −0.25 A, V_{GEN} = −4.5 V, R_g = 10 Ω	N-Ch		7	12	ns
			P-Ch		7	12	
Rise Time	t_r		N-Ch		25	35	
			P-Ch		25	35	
Turn-Off Delay Time	$t_{d(off)}$		N-Ch		19	30	
			P-Ch		19	30	
Fall Time	t_f		N-Ch		9	15	
			P-Ch		9	15	

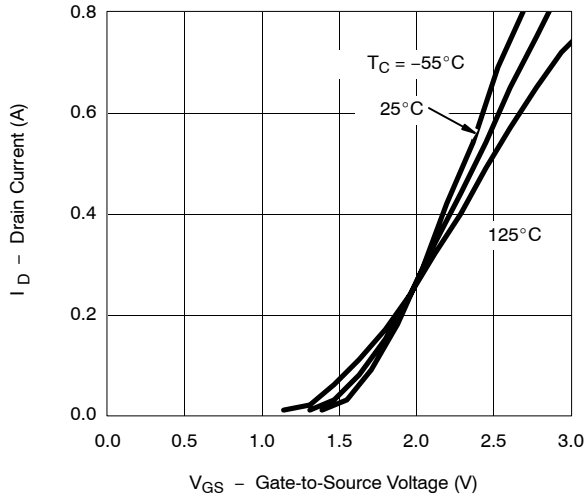
Notes
a. Guaranteed by design, not subject to production testing.
b. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED) N-CHANNEL

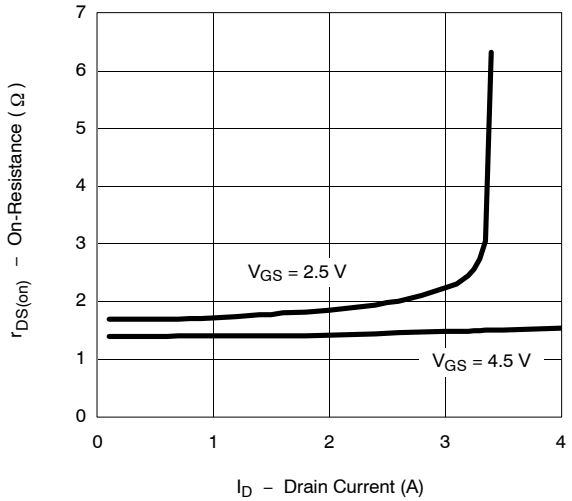
Output Characteristics



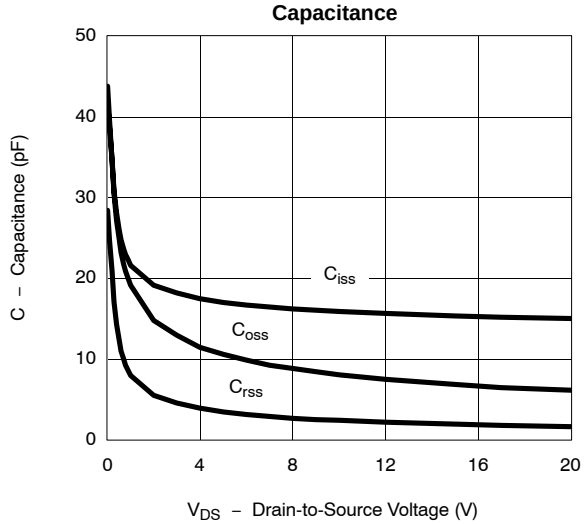
Transfer Characteristics



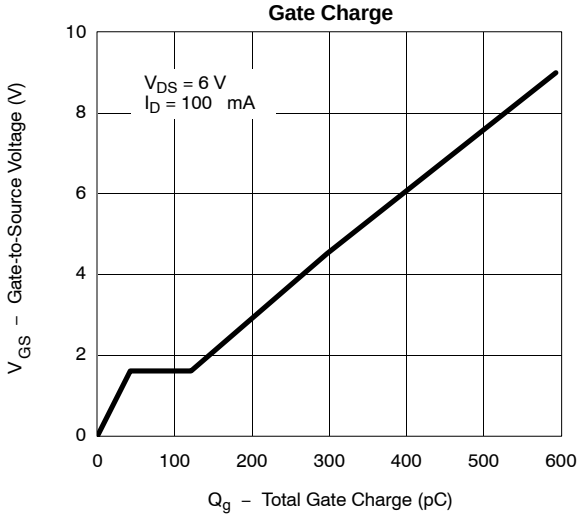
On-Resistance vs. Drain Current



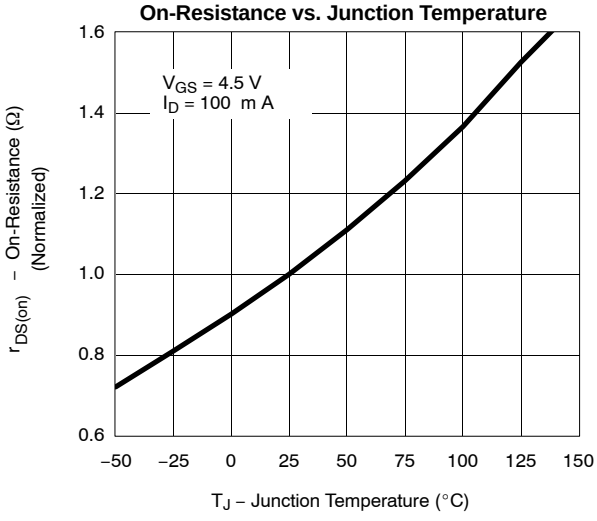
Capacitance



Gate Charge

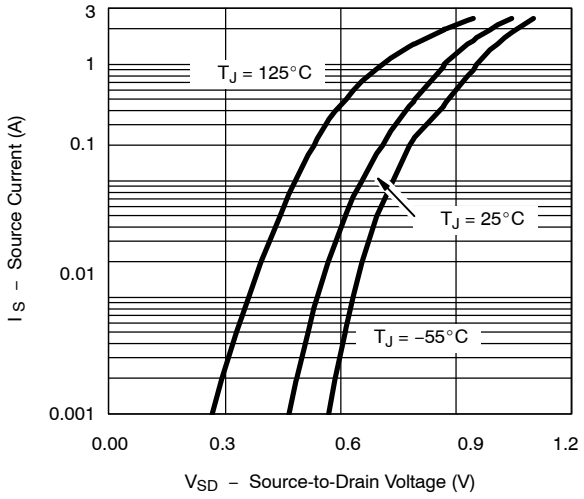


On-Resistance vs. Junction Temperature

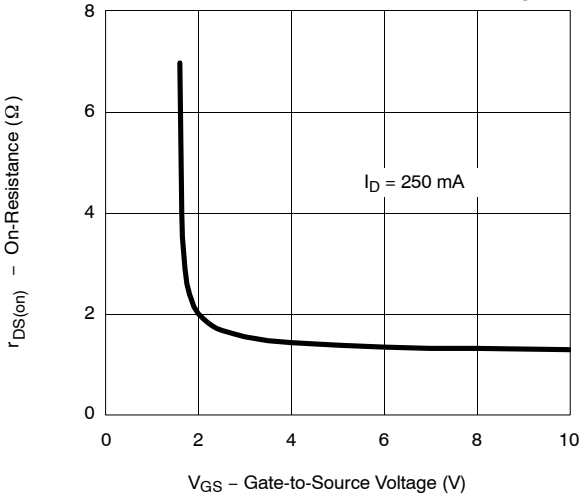


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED) N-CHANNEL

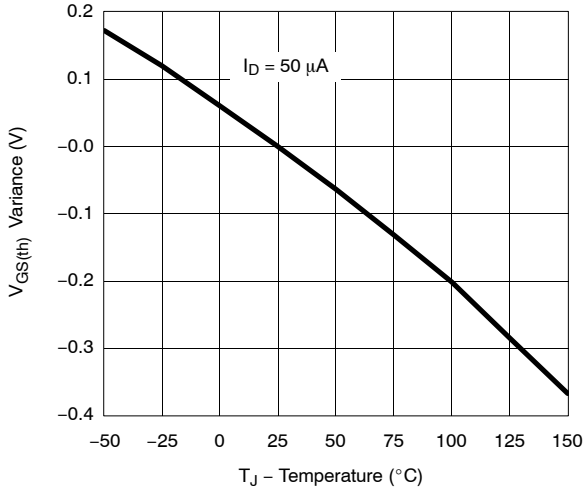
Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage

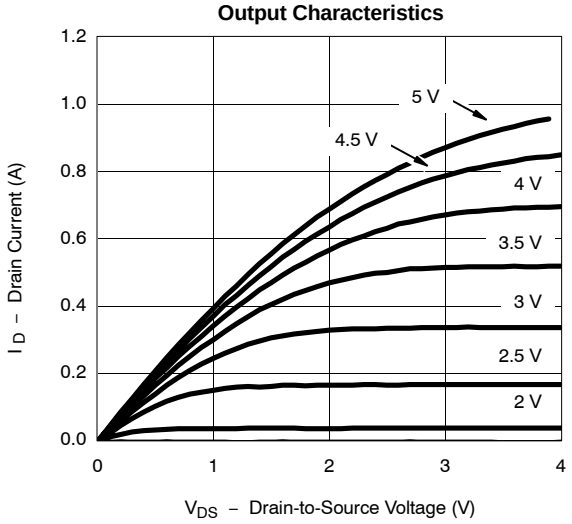


Threshold Voltage

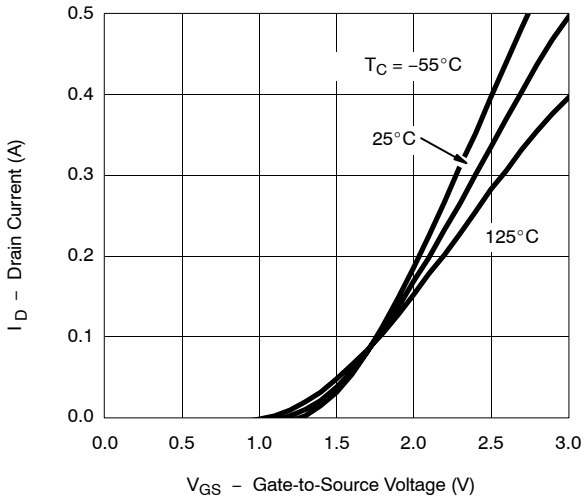


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED) P-CHANNEL

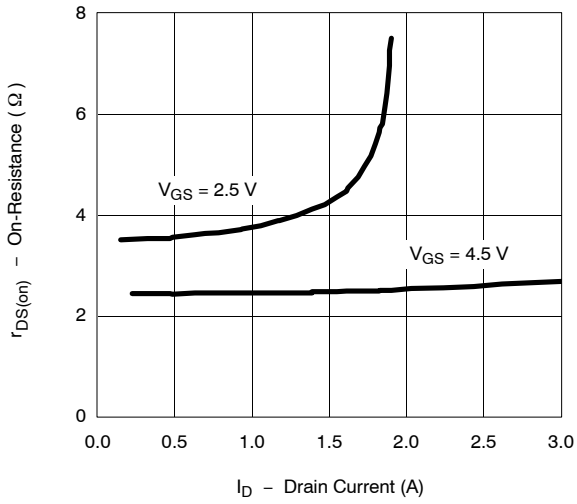
Output Characteristics



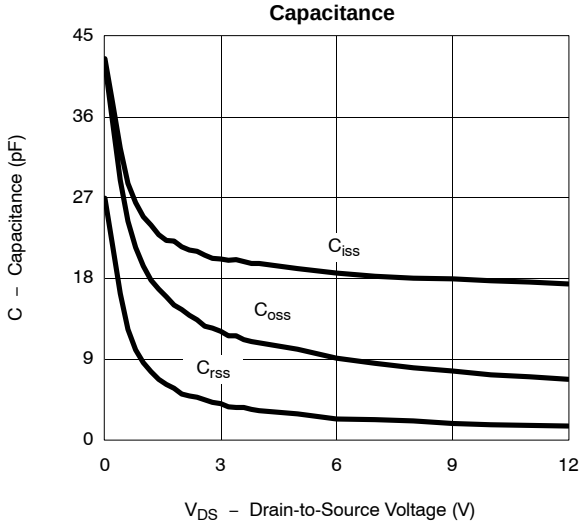
Transfer Characteristics



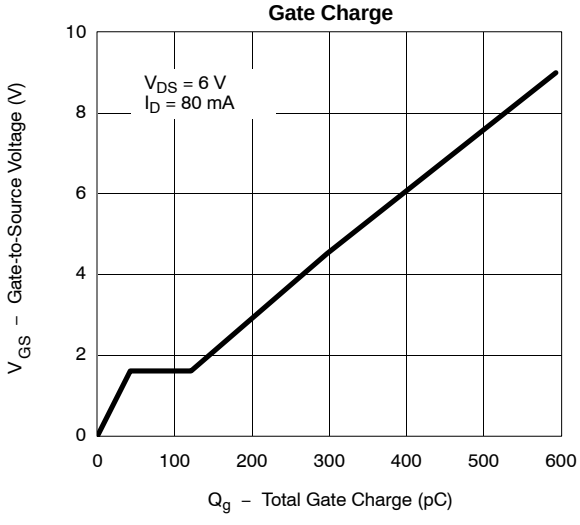
On-Resistance vs. Drain Current



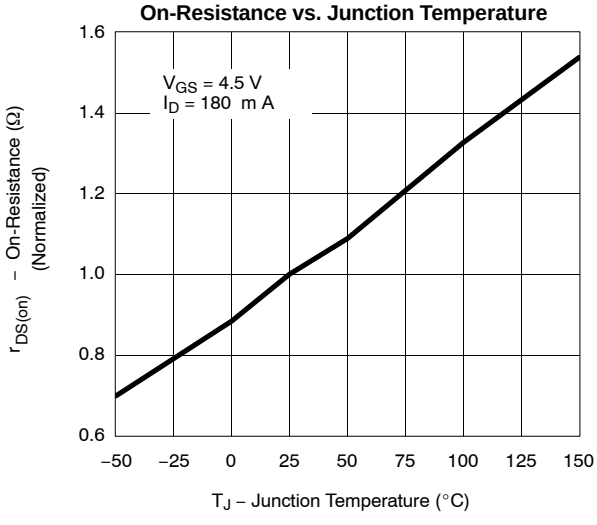
Capacitance



Gate Charge

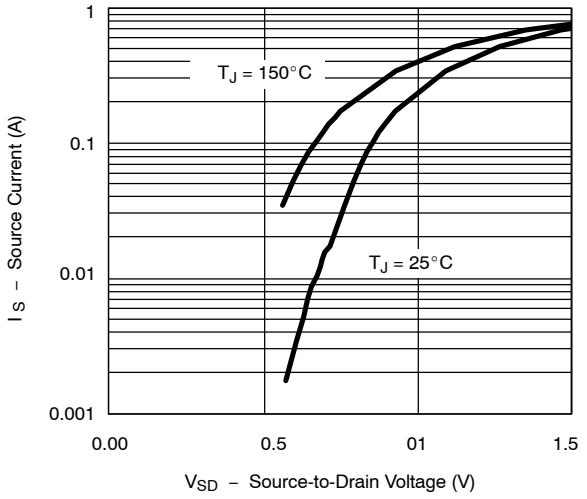


On-Resistance vs. Junction Temperature

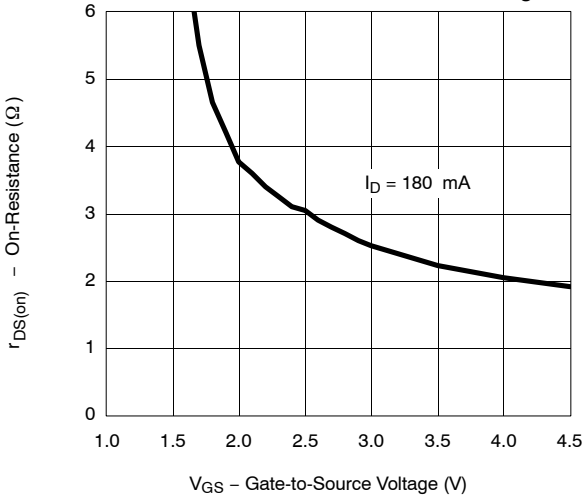


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED) P-CHANNEL

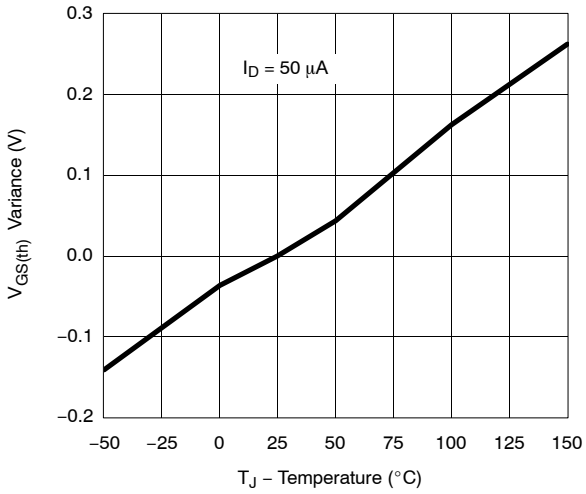
Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



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